



VDRM

T(AV)

Iтsм dV/dt*

dl/dt

KEY PARAMETERS

8500V

3910A

58100A

2000V/µs

500A/µs

* Higher dV/dt selections are available on request



Replaces DS6139-2

Phase Control Thyristor

DS6139-3 September 2021 (LN41127)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
DCR3980H85* DCR3980H80 DCR3980H75	8500 8000 7500	$T_{vj} = -40^{\circ}C \text{ to } 125^{\circ}C,$ IDRM = IRRM = 600MA, $VDRM, VRRM t_P = 10ms$ VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

*8200V @ -40°C, 8500V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3980H85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

Outline type code: H

Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	3910	А
It(rms)	RMS value	-	6140	А
Гт	Continuous (direct) on-state current	-	5740	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	58.1	kA
l²t	I ² t for fusing	VR = 0	16.9	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditior	Min.	Max.	Units	
		Double side cooled DC		-	4.3	°C/kW
Rth(j-c)	Rth(j-c) Thermal resistance - junction to case	Single side cooled	Anode DC	-	8.0	°C/kW
		Single side cooled	Cathode DC	-	9.5	°C/kW
Back	Thermal resistance - case to	Clamping force 135kN	Double side	-	0.9	°C/kW
Rth(c-h)	heatsink	(with mounting compound)	Single side	-	1.8	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			120	155	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	Test Conditions			Units
Irrm/Idrm	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C		-	600	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.90	2.20	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Tj = 125°C, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 Ω	Repetitive 50Hz	-	200	A/µs
avat		$tr < 0.5\mu s, T_j = 125^{\circ}C$	Non-repetitive	-	500	A/µs
	Threshold voltage - Low level	1000A to 3800A at Tcase = 1	-	1.03	V	
V τ(το)	Threshold voltage - High level	3800A to 8000A at Tcase = 1	-	1.26	V	
	On-state slope resistance - low level	1000A to 3800A at Tcase = 125°C			0.30	mΩ
ľτ	On-state slope resistance - High level	3800A to 8000A at Tcase = 1	-	0.24	mΩ	
tgd	Delay time	V_D = 67% V_{DRM} , gate source 30V, 10 Ω tr = 0.5µs, Tj = 25°C		-	3	μs
tq	Turn-off time	IT = 3000A, Tj = 125°C, VR = 200V, dl/dt = 1A/ μ s, dVDR/dt = 20V/ μ s linear		-	1000	μs
Qs	Stored charge	Iт = 3000A, Tj = 125°C, dl/dt = 1A/µs VR(peak) ~ 5100V, VRм ~ 3400V		4900	10600	μC
Irr	Reverse recovery current			54	87	А
lı.	Latching current $T_j = 25^{\circ}C, V_D = 5V$			-	3	А
Ін	Holding current	Tj = 25°C, R _{G-} к = ∞, Iтм = 500А, Iт = 5А		-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrm = 5V, Tcase = 25°C	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrм = 5V, Tcase = 25°С	350	mA
Igd	Gate non-trigger current	At 50% Vdrм, Tcase = 125°С	10	mA

CURVES

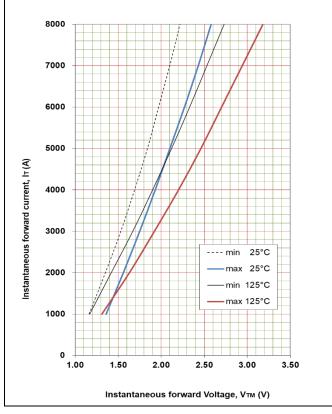


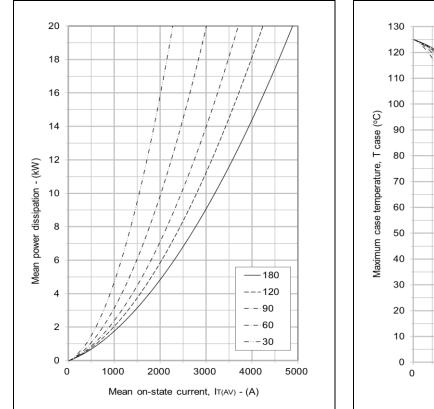
Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.399542 B = 0.072270 C = 0.000187 D = 0.007086 These values are valid for T_j = 125°C for I_T 1000A to 8000A

DCR3980H85



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Fig. 3 On-state power dissipation - sine wave

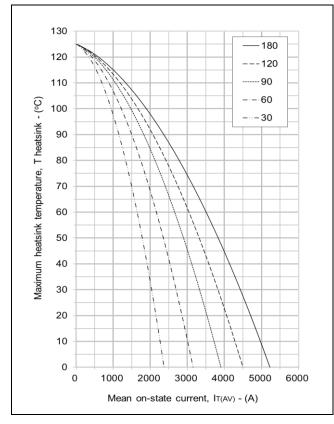


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

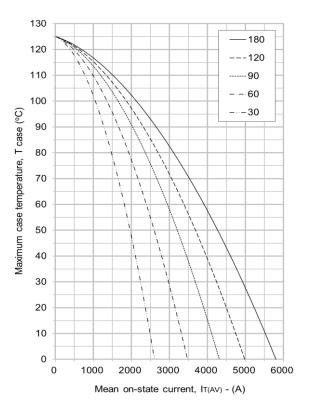


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

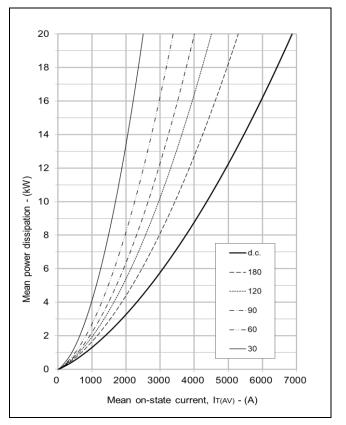


Fig. 6 On-state power dissipation - rectangular wave

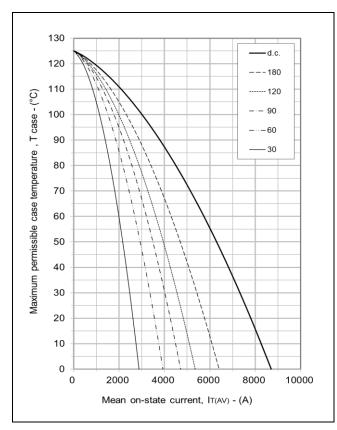
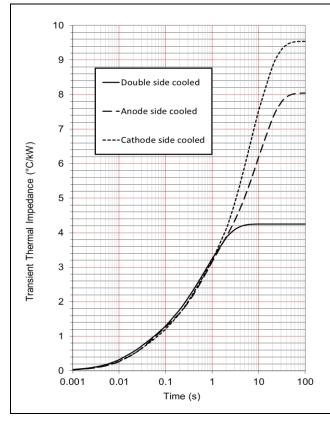


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



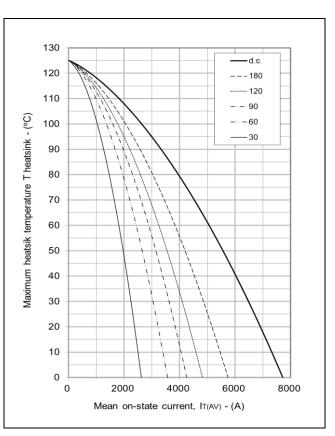


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side cooled	Ri(°C/kW)	1.248	0.833	0.606	1.568
Double side cooled	Ti(s)	0.670	0.146	0.020	1.287
Anode side cooled	Ri(°C/kW)	0.512	1.946	0.920	4.666
	Ti(s)	2.898	0.505	0.036	10.647
Cathode side	Ri(°C/kW)	2.417	1.537	0.626	4.959
cooled	Ti(s)	3.441	0.269	0.024	10.172

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

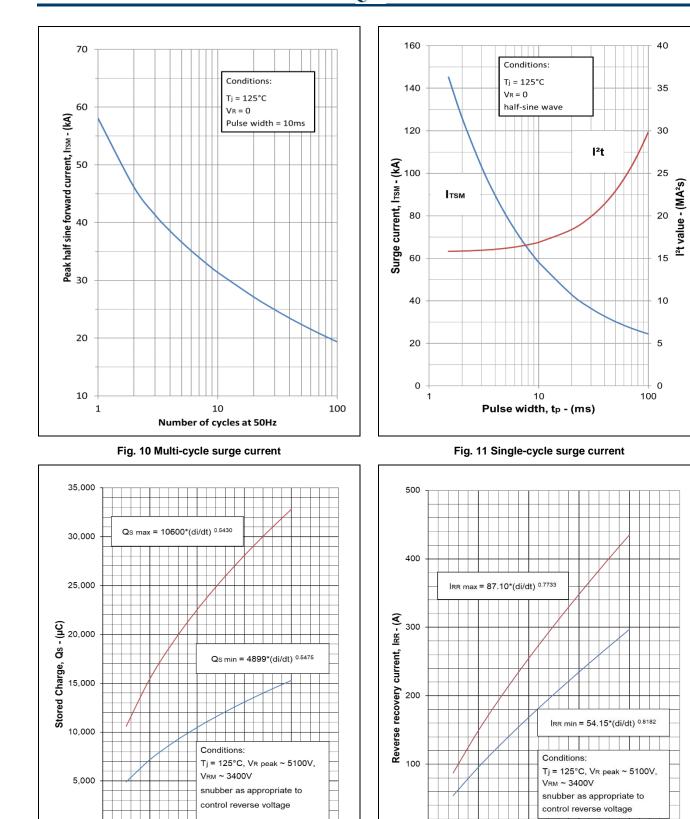
 $\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance R $_{\text{frij-ej}}$ when the device operates at conduction angles other than d.c.

D	ouble side c	ooling	Ar	ode Side Cooling			Cathode Sided Cooling		
	ΔZ_{th}	(z)		ΔZ	_h (z)			ΔZ	th (Z)
θ°	sine.	rect.	θ°	sine.	rect.		θ°	sine.	rect.
180	0.38	0.26	180	0.32	0.23		180	0.33	0.23
120	0.44	0.37	120	0.36	0.31		120	0.38	0.33
90	0.49	0.43	90	0.41	0.36		90	0.43	0.37
60	0.54	0.49	60	0.45	0.40		60	0.47	0.43
30	0.58	0.55	30	0.48	0.45		30	0.51	0.48
15	0.60	0.58	15	0.49	0.48		15	0.52	0.51



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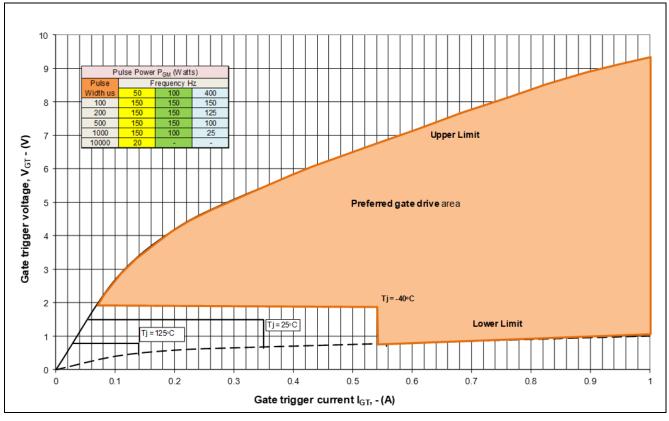
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Rate of decay of on-state current, di/dt - (A/µs)

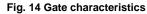
Fig. 12 Reverse recovery charge

Fig. 13 Reverse recovery current

Rate of decay of on-state current, di/dt - (A/µs)



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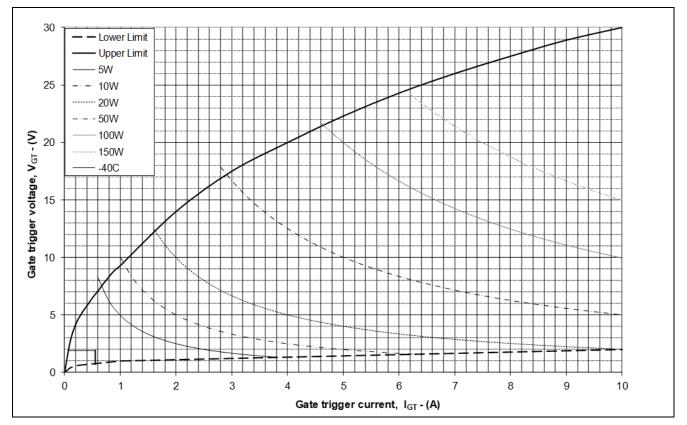


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

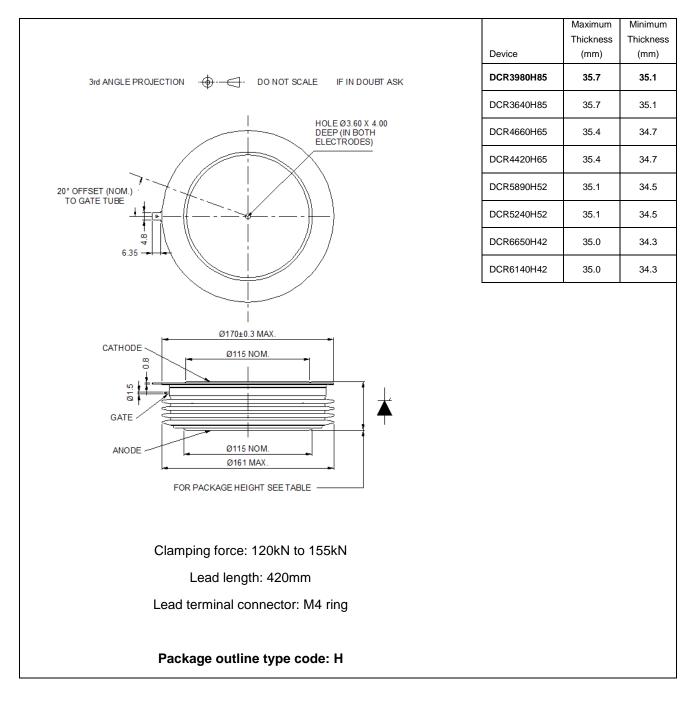


Fig. 16 Package outline

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